



Bipolar PNP Bare Die – BTP6027

Part Description

The BTP6027 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = -30V
- VCEO = -30V
- VEBO = -6V
- hFE = 120-390 @ VCE = -2V, IC = -0.1A
- VCE(Sat) = -0.5V @ IC = -2A, IB = -100mA
- fT = 190 MHz @ VCE = -10V, IE = 0A
- COBO = 35pF @ VCB = -10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to ROHM 2SB1424

Die Size (Unawn)

790µm X 790µm, 31 Mils X 31 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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